

isc Silicon NPN Power Transistor

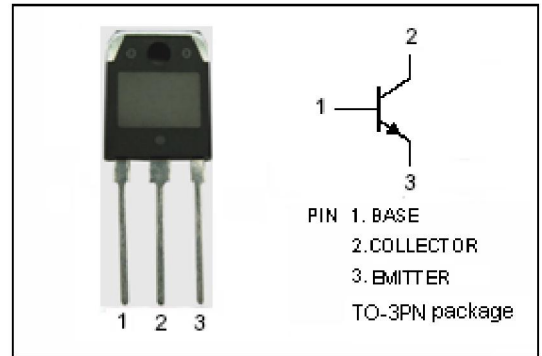
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DESCRIPTION

- High Collector-Emitter Breakdown Voltage-
: $V_{(BR)CEO} = 400V(\text{Min})$
- High Switching Speed
- High Reliability

APPLICATIONS

- Switching regulators
- Ultrasonic generators
- High frequency inverters
- General purpose power amplifiers

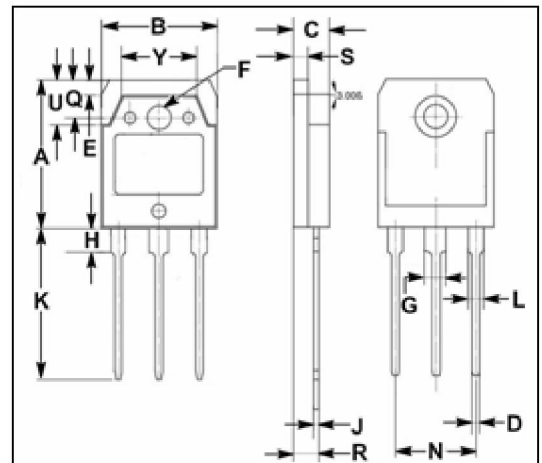


ABSOLUTE MAXIMUM RATINGS($T_a=25^\circ\text{C}$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	500	V
V_{CEO}	Collector-Emitter Voltage	400	V
$V_{CEO(SUS)}$	Collector-Emitter Voltage	400	V
V_{EBO}	Emitter-Base Voltage	7	V
I_C	Collector Current-Continuous	15	A
I_B	Base Current-Continuous	5	A
P_C	Collector Power Dissipation @ $T_c=25^\circ\text{C}$	80	W
T_J	Junction Temperature	150	$^\circ\text{C}$
T_{stg}	Storage Temperature Range	-65~150	$^\circ\text{C}$

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j-c}$	Thermal Resistance, Junction to Case	1.56	$^\circ\text{C/W}$



DIM	mm	
	MIN	MAX
A	19.90	20.10
B	15.50	15.70
C	4.70	4.90
D	0.90	1.10
E	1.90	2.10
F	3.40	3.60
G	2.90	3.10
H	3.20	3.40
J	0.595	0.605
K	20.50	20.70
L	1.90	2.10
N	10.89	10.91
Q	4.90	5.10
R	3.35	3.45
S	1.995	2.005
U	5.90	6.10
Y	9.90	10.10

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ELECTRICAL CHARACTERISTICS

 $T_C=25^{\circ}\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	$I_C=10\text{mA}; I_B=0$	400			V
$V_{CEO(SUS)}$	Collector-Emitter Sustaining Voltage	$I_C=0.2\text{A}; I_B=0$	400			V
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage	$I_C=1\text{mA}; I_E=0$	500			V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	$I_E=1\text{mA}; I_C=0$	7			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C=6\text{A}; I_B=1.2\text{A}$			1.0	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	$I_C=6\text{A}; I_B=1.2\text{A}$			1.5	V
I_{CBO}	Collector Cutoff Current	$V_{CB}=500\text{V}; I_E=0$			1.0	mA
I_{EBO}	Emitter Cutoff Current	$V_{EB}=7\text{V}; I_C=0$			1.0	mA
h_{FE}	DC Current Gain	$I_C=6\text{A}; V_{CE}=5\text{V}$	10			

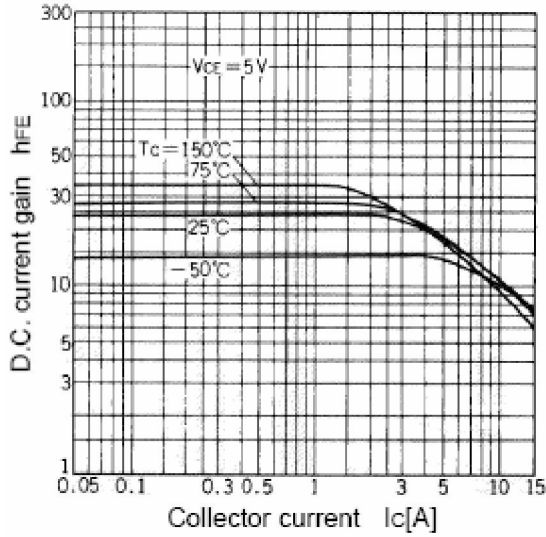
Switching times

t_{on}	Turn-on Time	$I_C=7.5\text{A}, I_{B1}=1.5\text{A}; I_{B2}=-3\text{A}$ $R_L=20\Omega; P_W=20\mu\text{s Duty}\leq 2\%$			0.5	μs
t_{stg}	Storage Time				1.5	μs
t_f	Fall Time				0.15	μs

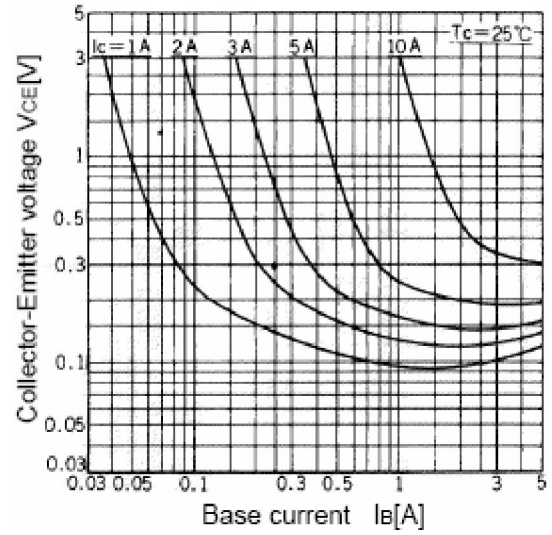
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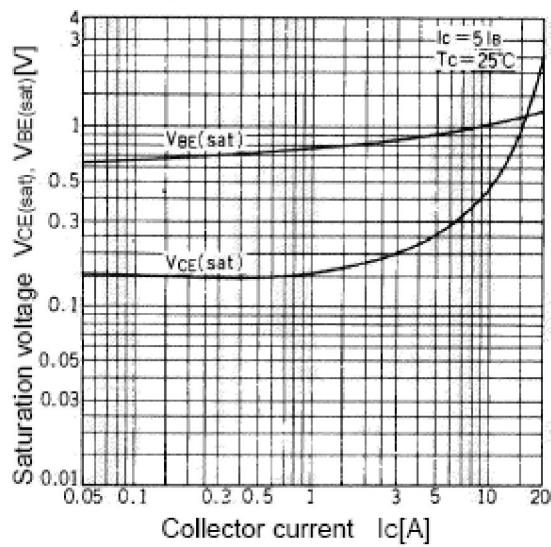
$h_{FE}-I_C$ Characteristics



$V_{CE(sat)}-I_B$ Characteristics



$V_{CE(sat)}-I_C$ & $V_{BE(sat)}-I_C$ Characteristics



Safe Operating Area

